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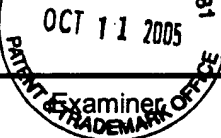
TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(e))				Docket No. YOR920030602US1	
In Re Application Of: Joel P. de Souza et al.					
Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/725,850	December 2, 2003	Dao H. Nguyen	23389	2818	3232
Title: PLANAR SUBSTRATE WITH SELECTED SEMICONDUCTOR CRYSTAL ORIENTATIONS FORMED BY LOCALIZED AMORPHIZATION AND RECRYSTALLIZATION OF STACKED TEMPLATE LAYERS					
Address to: Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450					
37 CFR 1.97(b)					
1. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.					
37 CFR 1.97(c)					
2. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:					
<div style="margin-left: 40px;"> <input checked="" type="checkbox"/> the statement specified in 37 CFR 1.97(e); </div>					
OR					
<div style="margin-left: 40px;"> <input type="checkbox"/> the fee set forth in 37 CFR 1.17(p). </div>					

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

(Under 37 CFR 1.97(b) or 1.97(s))

Docket No.
YOR920030602US1

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Title: **PLANAR SUBSTRATE WITH SELECTED SEMICONDUCTOR CRYSTAL ORIENTATIONS FORMED BY LOCALIZED AMORPHIZATION AND RECRYSTALLIZATION OF STACKED TEMPLATE LAYERS**

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **50-0510/IBM** as described below.
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October 7, 2005

(Date)

Signature of Person Mailing Correspondence

Leslie S. Szivos, Ph.D.

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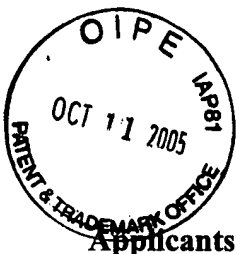
Signature

Dated: October 7, 2005

Leslie S. Szivos, Ph.D.
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	Joel de Souza et al.	Docket:	YOR920030602US1 (17242)
Serial No.:	10/725,850	Examiner:	Dao H. Nguyen
Filed:	December 2, 2003	Art Unit:	2818
For:	PLANAR SUBSTRATE WITH SELECTED SEMICONDUCTOR CRYSTAL ORIENTATIONS FORMED BY LOCALIZED AMORPHIZATION AND RECRYSTALLIZATION OF STACKED TEMPLATE LAYERS	Dated:	October 7, 2005
		Confirmation No:	3232

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

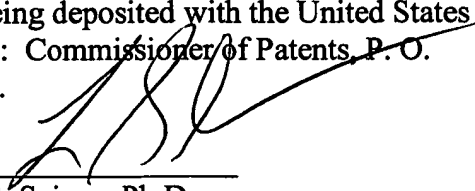
In accordance with 37 C.F.R. §§ 1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case.

1. United States Patent Application Publication Number 2005/0016290 dated June 2, 2005, issued to de Souza et al.;

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on October 7, 2005.

Dated: October 7, 2005



Leslie S. Szivos, Ph.D.

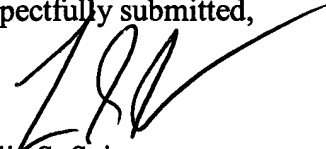
2. United States Patent Number 5,384,473 dated January 24, 1995, issued to Yoshikawa et al.;
3. United States Patent Number 6,815,278 B1 dated November 9, 2004, issued to Icong et al.;
4. Csepregi, L. et al., Substrate-orientation dependence of the epitaxial regrowth rate from Si-implanted amorphous Si, 49:7 *J. Appl. Phys.* 3906, 3906-10, (1978).
5. 6th International Symposium on Semiconductor Wafer Bonding, *An investigation into interfacial oxide in direct silicon bonding*, (September 2001); and
6. Solid State Technology, *SOI wafers based on epitaxial technology*, (2000), available at http://sst.pennnet.com/articles/article_display.cfm?Section=ARCHI&C=Feat&ARTICLE_ID=75323&KEYWORDS=K%2E%20Sakaguchi&p=5.

Applicants are submitting copies of the above-cited references.

In accordance with the waiver of 37 C.F.R. § 1.98 (a)(2)(i) in effect as of June 30, 2003, applicants are not required to submit copies of the above-cited U.S. Patent references.

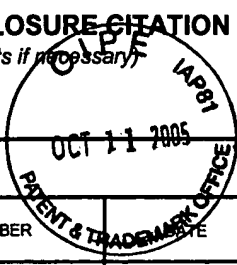
No item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and to the knowledge of the undersigned, after making reasonable inquiry, no item of information was known to any individual designated in §1.56(c) more than three months prior to the filing of the information disclosure statement.

Respectfully submitted,


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Enclosure PTO 1449

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. YOR920030602US1 (17242)		APPLICATION NO. 10/725,850	
				APPLICANT(S) Joel P. de Souza et al.			
FILING DATE December 2, 2003				GROUP ART UNIT 2818			



U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,384,473	01/24/1995	Yoshikawa et al.			
		6,815,278 B1	11/09/2004	Icong et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		2005/0016290	06/02/2005	deSouza et al.			

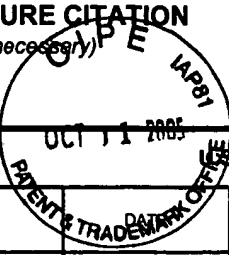
FOREIGN PATENT DOCUMENTS									
*	EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
								YES	NO

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>			
*	EXAMINER INITIAL		Csepregi, L. et al., Substrate-orientation dependence of the epitaxial regrowth rate from Si-implanted amorphous Si, 49:7 <i>J. Appl. Phys.</i> 3906, 3906-10, (1978);
			6th International Symposium on Semiconductor Wafer Bonding, <i>An investigation into interfacial oxide in direct silicon bonding</i> , (September 2001); and

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. YOR920030602US1 (17242)		APPLICATION NO. 10/725,850	
				Joel P. de Souza et al. FILING December 2, 2005 GROUP ART 2818			



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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>			
			Solid State Technology, <i>SOI wafers based on epitaxial technology</i> , (2000), available at http://sst.pennnet.com/articles/article_display.cfm?Section=ARCHI&CFat&ARTICLE_ID75323&KEYWORDS=K%2E%20Sakaguchi&p=5

EXAMINER	DATE CONSIDERED

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